Quad Analog Switch/ Multiplexer/Demultiplexer

High-Performance Silicon-Gate CMOS

The MC74HC4066A utilizes silicon–gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF-channel leakage current. This bilateral switch/multiplexer/demultiplexer controls analog and digital voltages that may vary across the full power–supply range (from V_{CC} to GND).

The HC4066A is identical in pinout to the metal–gate CMOS MC14016 and MC14066. Each device has four independent switches. The device has been designed so the ON resistances (R_{ON}) are more linear over input voltage than R_{ON} of metal–gate CMOS analog switches.

The ON/OFF control inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs. For analog switches with voltage–level translators, see the HC4316A.

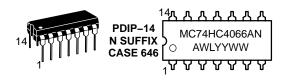
Features

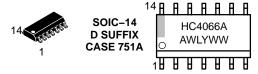
- Fast Switching and Propagation Speeds
- High ON/OFF Output Voltage Ratio
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Wide Power–Supply Voltage Range $(V_{CC} GND) = 2.0$ to 12.0 Volts
- Analog Input Voltage Range $(V_{CC} GND) = 2.0$ to 12.0 Volts
- Improved Linearity and Lower ON Resistance over Input Voltage than the MC14016 or MC14066
- Low Noise
- Chip Complexity: 44 FETs or 11 Equivalent Gates
- Pb-Free Packages are Available*



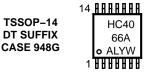
http://onsemi.com

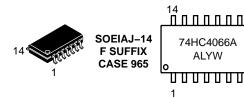
MARKING DIAGRAMS









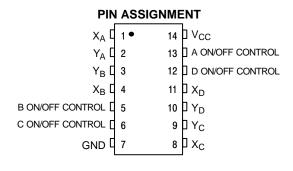


A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week

ORDERING INFORMATION

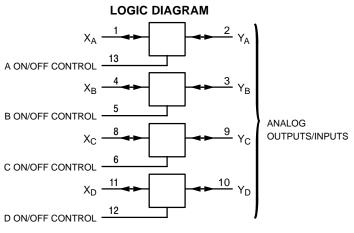
See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



FUNCTION TABLE

Analog Switch
Off On



ANALOG INPUTS/OUTPUTS = X_A , X_B , X_C , X_D PIN 14 = V_{CC} PIN 7 = GND

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC4006AN	PDIP-14	500 Units / Rail
MC74HC4006ANG	PDIP-14 (Pb-Free)	500 Units / Rail
MC74HC4006AD	SOIC-14	55 Units / Rail
MC74HC4006ADR2	SOIC-14	2500 Tape & Reel
MC74HC4006ADR2G	SOIC-14 (Pb-Free)	2500 Tape & Reel
MC74HC4006ADTR2	TSSOP-14*	2500 Tape & Reel
MC74HC4006AFEL	SOEIAJ-14	2000 Tape & Reel
MC74HC4006AFELG	SOEIAJ-14 (Pb-Free)	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *This package is inherently Pb–Free.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open. I/O pins must be connected to a properly terminated line or bus.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage (Referenced to GND)	- 0.5 to + 14.0	V
V _{IS}	Analog Input Voltage (Referenced to GND)	– 0.5 to V _{CC} + 0.5	V
V _{in}	Digital Input Voltage (Referenced to GND)	– 0.5 to V _{CC} + 0.5	V
I	DC Current Into or Out of Any Pin	± 25	mA
P _D	Power Dissipation in Still Air, Plastic DIP† EIAJ/SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C

EIAJ/SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage (Referenced to GND)	2.0	12.0	V
V _{IS}	Analog Input Voltage (Referenced to GND)	GND	V _{CC}	V
V _{in}	Digital Input Voltage (Referenced to GND)	GND	V _{CC}	V
V _{IO} *	Static or Dynamic Voltage Across Switch	_	1.2	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time, ON/OFF Control Inputs (Figure 10) $ \begin{array}{c} V_{CC}=2.0 \ V \\ V_{CC}=3.0 \ V \\ V_{CC}=4.5 \ V \\ V_{CC}=9.0 \ V \\ V_{CC}=12.0 \ V \end{array} $	0 0 0 0	1000 600 500 400 250	ns

^{*}For voltage drops across the switch greater than 1.2 V (switch on), excessive V_{CC} current may be drawn; i.e., the current out of the switch may contain both V_{CC} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

DC ELECTRICAL CHARACTERISTIC Digital Section (Voltages Referenced to GND)

				Gu	Guaranteed Lim		
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Voltage ON/OFF Control Inputs	R _{on} = Per Spec	2.0 3.0 4.5 9.0 12.0	1.5 2.1 3.15 6.3 8.4	1.5 2.1 3.15 6.3 8.4	1.5 2.1 3.15 6.3 8.4	V
V _{IL}	Maximum Low–Level Voltage ON/OFF Control Inputs	R _{on} = Per Spec	2.0 3.0 4.5 9.0 12.0	0.5 0.9 1.35 2.7 3.6	0.5 0.9 1.35 2.7 3.6	0.5 0.9 1.35 2.7 3.6	V
I _{in}	Maximum Input Leakage Current ON/OFF Control Inputs	V _{in} = V _{CC} or GND	12.0	± 0.1	± 1.0	± 1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND V _{IO} = 0 V	6.0 12.0	2 4	20 40	40 160	μΑ

NOTE: Information on typical parametric values can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

DC ELECTRICAL CHARACTERISTICS Analog Section (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	v _{cc} v	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
R _{on}	Maximum "ON" Resistance	$V_{in} = V_{IH}$ $V_{IS} = V_{CC}$ to GND $I_{S} \le 2.0$ mA (Figures 1, 2)	2.0† 3.0† 4.5 9.0 12.0	- - 120 70 70	- 160 85 85	- 200 100 100	Ω
		$\begin{aligned} & V_{\text{in}} = V_{\text{IH}} \\ & V_{\text{IS}} = V_{\text{CC}} \text{ or GND} \\ & (\text{Endpoints}) \\ & I_{\text{S}} \leq 2.0 \text{ mA (Figures 1, 2)} \end{aligned}$	2.0 3.0 4.5 9.0 12.0	- - 70 50 50	- - 85 60 60	- - 120 80 80	
ΔR _{on}	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$\begin{aligned} &V_{in} = V_{IH} \\ &V_{IS} = 1/2 \left(V_{CC} - GND \right) \\ &I_{S} \leq 2.0 \text{ mA} \end{aligned}$	2.0 4.5 9.0 12.0	- 20 15 15	- 25 20 20	- 30 25 25	Ω
l _{off}	Maximum Off–Channel Leakage Current, Any One Channel	$V_{in} = V_{IL}$ $V_{IO} = V_{CC}$ or GND Switch Off (Figure 3)	12.0	0.1	0.5	1.0	μΑ
I _{on}	Maximum On–Channel Leakage Current, Any One Channel	$V_{in} = V_{IH}$ $V_{IS} = V_{CC}$ or GND (Figure 4)	12.0	0.1	0.5	1.0	μΑ

[†]At supply voltage (V_{CC}) approaching 3 V the analog switch–on resistance becomes extremely non–linear. Therefore, for low–voltage operation, it is recommended that these devices only be used to control digital signals.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, ON/OFF Control Inputs: $t_f = t_f = 6 \text{ ns}$)

				Gua	Guaranteed Limit		
Symbol	Parameter		V _{CC} V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Analog Input (Figures 8 and 9)	to Analog Output	2.0 3.0 4.5 9.0 12.0	40 30 10 10	50 40 13 13	60 50 15 15	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, ON/OFF Con (Figures 10 and 11)	trol to Analog Output	2.0 3.0 4.5 9.0 12.0	80 60 30 25 25	90 70 38 28 28	110 80 45 30 30	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, ON/OFF Con (Figures 10 and 1 1)	trol to Analog Output	2.0 3.0 4.5 9.0 12.0	80 45 25 25 25	90 50 32 32 32	100 60 37 37 37	ns
С	Maximum Capacitance	ON/OFF Control Input Control Input = GND Analog I/O Feedthrough	- - -	10 35 1.0	10 35 1.0	10 35 1.0	pF

NOTES:

- 1. For propagation delays with loads other than 50 pF, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).
- 2. Information on typical parametric values can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Switch) (Figure 13)*	15	pF

^{*}Used to determine the no-load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

NOTE: Information on typical parametric values can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

Symbol	Parameter	Test Conditions	V _{CC}	Limit* 25°C 54/74HC	Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response (Figure 5)	$\begin{aligned} f_{in} &= 1 \text{ MHz Sine Wave} \\ &\text{Adjust } f_{in} \text{ Voltage to Obtain 0 dBm at V}_{OS} \\ &\text{Increase } f_{in} \text{ Frequency Until dB Meter Reads} - 3 \text{ dB} \\ &R_L = 50 \ \Omega, \ C_L = 10 \text{ pF} \end{aligned}$	4.5 9.0 12.0	150 160 160	MHz
_	Off-Channel Feedthrough Isolation (Figure 6)	$ \begin{aligned} f_{in} &\equiv \text{Sine Wave} \\ \text{Adjust } f_{in} &\text{ Voltage to Obtain 0 dBm at V}_{IS} \\ f_{in} &= 10 \text{ kHz}, \text{ R}_{L} = 600 \ \Omega, \text{ C}_{L} = 50 \text{ pF} \end{aligned} $	4.5 9.0 12.0	- 50 - 50 - 50	dB
		f_{in} = 1.0 MHz, R_L = 50 Ω , C_L = 10 pF	4.5 9.0 12.0	- 40 - 40 - 40	
_	Feedthrough Noise, Control to Switch (Figure 7)	$\begin{split} V_{in} & \leq 1 \text{ MHz Square Wave } (t_r = t_f = 6 \text{ ns}) \\ \text{Adjust R}_L \text{ at Setup so that } I_S = 0 \text{ A} \\ \text{R}_L = 600 \ \Omega, \ C_L = 50 \text{ pF} \end{split}$	4.5 9.0 12.0	60 130 200	mV _{PP}
		$R_L = 10 \text{ k}\Omega$, $C_L = 10 \text{ pF}$	4.5 9.0 12.0	30 65 100	
_	Crosstalk Between Any Two Switches (Figure 12)	$\begin{split} f_{in} &\equiv \text{Sine Wave} \\ \text{Adjust } f_{in} &\text{ Voltage to Obtain 0 dBm at V}_{IS} \\ f_{in} &= 10 \text{ kHz}, \text{ R}_L = 600 \ \Omega, \text{ C}_L = 50 \text{ pF} \end{split}$	4.5 9.0 12.0	- 70 - 70 - 70	dB
		f_{in} = 1.0 MHz, R_L = 50 Ω , C_L = 10 pF	4.5 9.0 12.0	- 80 - 80 - 80	
THD	Total Harmonic Distortion (Figure 14)	$\begin{split} f_{in} = 1 \text{ kHz, } R_L = 10 \text{ k}\Omega \text{, } C_L = 50 \text{ pF} \\ \text{THD} = \text{THD}_{Measured} - \text{THD}_{Source} \\ V_{IS} = 4.0 \text{ V}_{PP} \text{ sine wave} \\ V_{IS} = 8.0 \text{ V}_{PP} \text{ sine wave} \\ V_{IS} = 11.0 \text{ V}_{PP} \text{ sine wave} \end{split}$	4.5 9.0 12.0	0.10 0.06 0.04	%

^{*}Guaranteed limits not tested. Determined by design and verified by qualification.

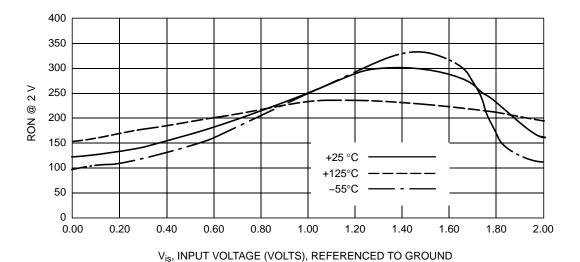


Figure 1a. Typical On Resistance, $V_{CC} = 2.0 \text{ V}$

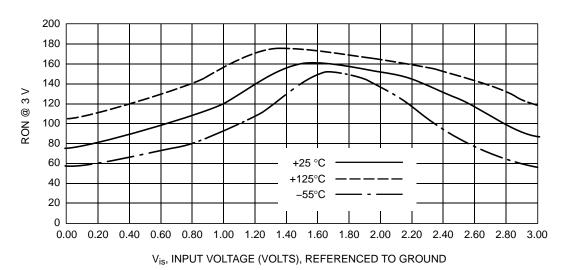


Figure 1b. Typical On Resistance, $V_{CC} = 3.0 \text{ V}$

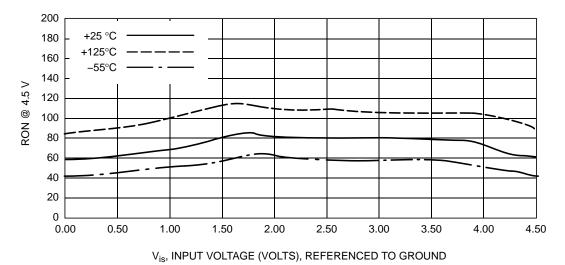
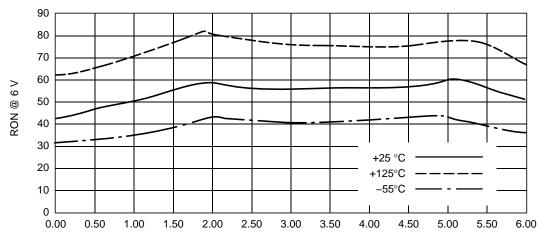


Figure 1c. Typical On Resistance, $V_{CC} = 4.5 \text{ V}$



Vis, INPUT VOLTAGE (VOLTS), REFERENCED TO GROUND

Figure 1d. Typical On Resistance, $V_{CC} = 6.0 \text{ V}$

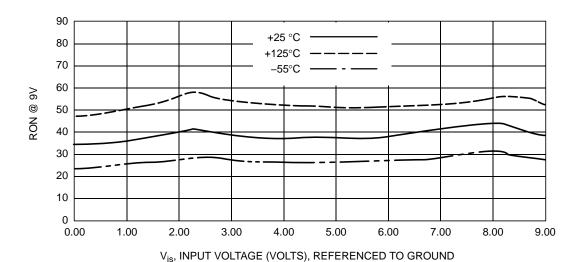


Figure 1e. Typical On Resistance, V_{CC} = 9.0 V

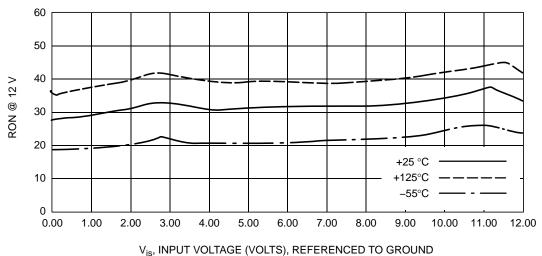


Figure 1f. Typical On Resistance, $V_{CC} = 12.0 \text{ V}$

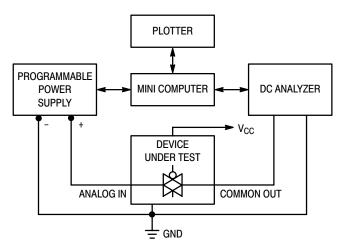
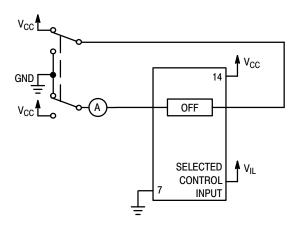


Figure 2. On Resistance Test Set-Up



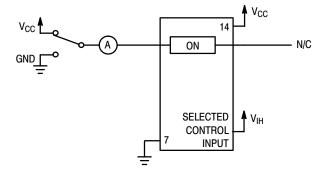
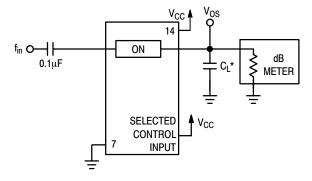


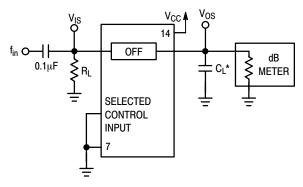
Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

Figure 4. Maximum On Channel Leakage Current, Test Set-Up



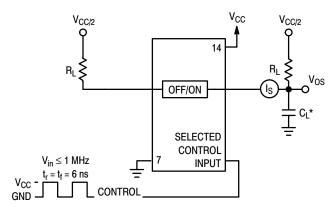
*Includes all probe and jig capacitance.

Figure 5. Maximum On-Channel Bandwidth
Test Set-Up



*Includes all probe and jig capacitance.

Figure 6. Off-Channel Feedthrough Isolation, Test Set-Up



*Includes all probe and jig capacitance.

Figure 7. Feedthrough Noise, ON/OFF Control to Analog Out, Test Set-Up

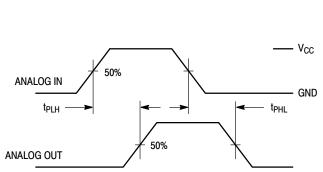
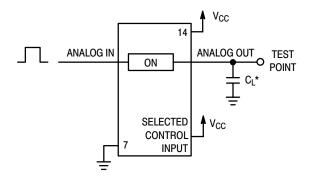
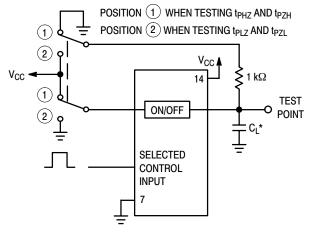


Figure 8. Propagation Delays, Analog In to Analog Out



^{*}Includes all probe and jig capacitance.

Figure 9. Propagation Delay Test Set-Up



^{*}Includes all probe and jig capacitance.

Figure 11. Propagation Delay Test Set-Up

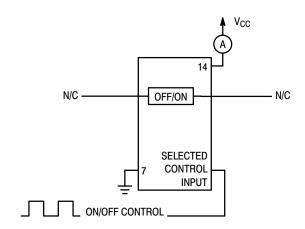


Figure 13. Power Dissipation Capacitance
Test Set-Up

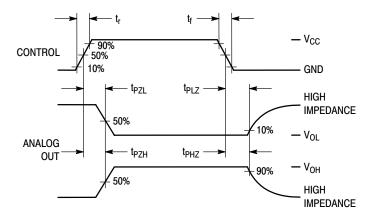
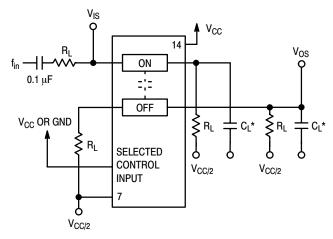
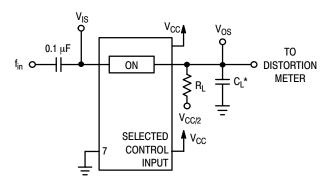


Figure 10. Propagation Delay, ON/OFF Control to Analog Out



^{*}Includes all probe and jig capacitance.

Figure 12. Crosstalk Between Any Two Switches, Test Set-Up



^{*}Includes all probe and jig capacitance.

Figure 14. Total Harmonic Distortion, Test Set-Up

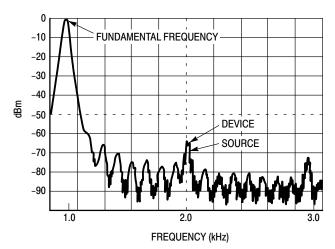


Figure 15. Plot, Harmonic Distortion

APPLICATION INFORMATION

The ON/OFF Control pins should be at V_{CC} or GND logic levels, V_{CC} being recognized as logic high and GND being recognized as a logic low. Unused analog inputs/outputs may be left floating (not connected). However, it is advisable to tie unused analog inputs and outputs to V_{CC} or GND through a low value resistor. This minimizes crosstalk and feedthrough noise that may be picked—up by the unused I/O pins.

The maximum analog voltage swings are determined by the supply voltages V_{CC} and GND. The positive peak analog voltage should not exceed V_{CC} . Similarly, the negative peak analog voltage should not go below GND. In the example

below, the difference between V_{CC} and GND is twelve volts. Therefore, using the configuration in Figure 16, a maximum analog signal of twelve volts peak—to—peak can be controlled.

When voltage transients above V_{CC} and/or below GND are anticipated on the analog channels, external diodes (Dx) are recommended as shown in Figure 17. These diodes should be small signal, fast turn—on types able to absorb the maximum anticipated current surges during clipping. An alternate method would be to replace the Dx diodes with Mosorbs (MosorbTM is an acronym for high current surge protectors). Mosorbs are fast turn—on devices ideally suited for precise DC protection with no inherent wear out mechanism.

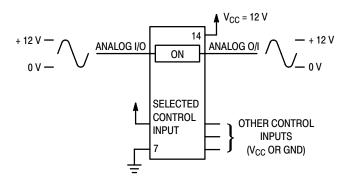


Figure 16. 12 V Application

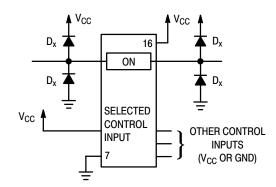
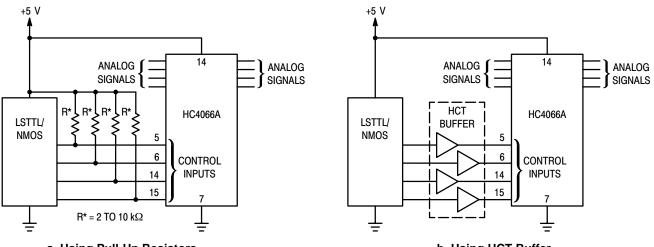


Figure 17. Transient Suppressor Application



a. Using Pull-Up Resistors

b. Using HCT Buffer

Figure 18. LSTTL/NMOS to HCMOS Interface

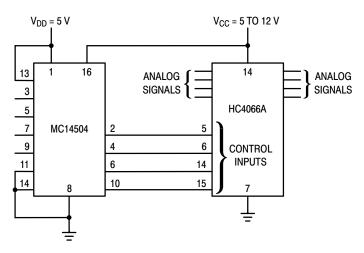


Figure 19. TTL/NMOS-to-CMOS Level Converter Analog Signal Peak-to-Peak Greater than 5 V (Also see HC4316A)

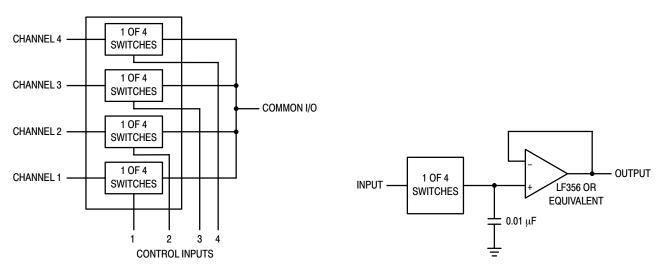
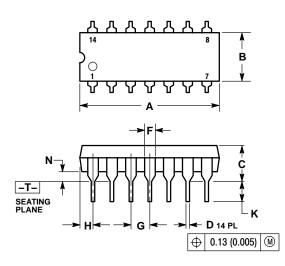


Figure 20. 4-Input Multiplexer

Figure 21. Sample/Hold Amplifier

PACKAGE DIMENSIONS

PDIP-14 **N SUFFIX** CASE 646-06 **ISSUE N**





NOTES:

- NOTES:

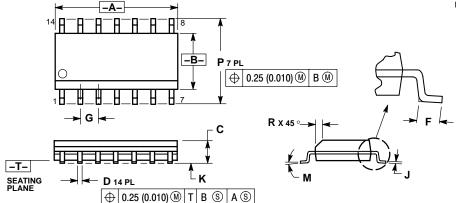
 1. DIMENSIONING AND TOLERANCING
 PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. DIMENSION L TO CENTER OF LEADS
 WHEN FORMED PARALLEL.
- VITEN FORWED FARALLEL.
 DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 ROUNDED CORNERS OPTIONAL.

	INCHES MILLIMETER			ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	18.80
В	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M		10 °		10 °
N	0.015	0.039	0.38	1.01

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE G**



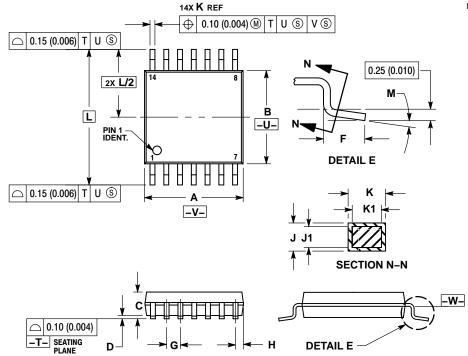
- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- 4. MAAIMUM MOLD PROTRUSION 0.15 (0.0)
 PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE
 DAMBAR PROTRUSION. ALLOWABLE
 DAMBAR PROTRUSION SHALL BE 0.127
 (0.005) TOTAL IN EXCESS OF THE D
 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

TSSOP-14 **DT SUFFIX** CASE 948G-01 **ISSUE A**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 - DIMENSION AT MAXIMUM MATERIAL CONDITION.

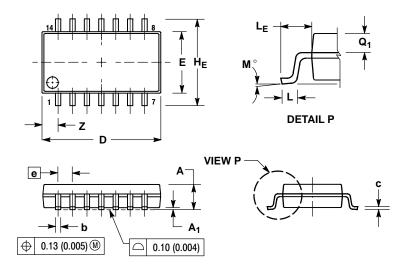
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0°	8 °	0 °	8 °	

PACKAGE DIMENSIONS

SOEIAJ-14 **F SUFFIX** CASE 965-01 **ISSUE O**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		1.42		0.056

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